OIPE APR 21 2004 PATENT & TRADEMARK OFFICE TC 2105

	ATTY. DOCKET NO.:	APPLICATION SERIAL NO.:
LIST OF REFERENCES CITED BY APPLICANT *(Use several sheets if necessary)*	4717-11400	10/686, 082
	APPLICANT: Bruno GHYSELEN et al.	
	FILING DATE: October 14, 2003	GROUP: 2812

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	4,771,016	9/1988	Bajor et al.	437	180	
	AB	5,517,047	5/1996	Linn et al.	257	347	
	AC	6,313,012 B1	11/2001	Horiuchi et al.	438	459	
	AD	6,410,938 B1	6/2002	Xiang	257	49	
	AE	2002/0070454 A1	6/2002	Yasukawa	257	760	
	AF	2004/0023468 A1	2/2004	Ghyselen et al.	438	455	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AG	FR 2 835 096 w/ English Abstract	7/2003	France			X	
	AH	WO 03063214 A2 (English Abstract of FR2835095)	7/2003	PCT			X	
	~~AI~~							

OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	AJ	N. Tate et al., "Defect Reduction of Bonded SOI Wafers by Post Anneal Process in H_2 Ambient," Proceedings 1998 IEEE International SOI Conference, pp. 141-142 (1998)
	~~AK~~	
	AL	
	AM	

EXAMINER	DATE CONSIDERED
Hanna Schulz	6/15/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

LIST OF REFERENCES CITED BY APPLICANT (*Use several sheets if necessary*)	ATTY. DOCKET NO.: 4717-11400	APPLICATION SERIAL NO.: 10/686 082
	APPLICANT: Bruno GHYSELEN et al.	
	FILING DATE: 10-14-03	GROUP: 2813

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	AG	FR2823599 English Abstract	10/2002	France			X	
	AH	WO 02084722	10/2002	PCT			X	
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	AJ	Q-Y. Tong and U. Gosele, "Semiconductor Wafer Bonding Science and Technology" ,Wiley Interscience publication, Johnson Wiley & Sons, Inc.
	AK	O. Rayssac et al , "Application for specific semiconductor processes" SOI to SOIM Technology, Electrochemical Society Proceedings, Vol. 2001-3, pp 39-44 (2001)
	AL	Olivier Rayssac et al., "Influence of Surface Characteristics on Direct Wafer Bonding", LETI/CEA Department de Microtechnologies, Genoble, France
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EXAMINER	DATE CONSIDERED
Marcia Schaefer	6/15/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.